

HF/VHF POWER MOS TRANSISTOR

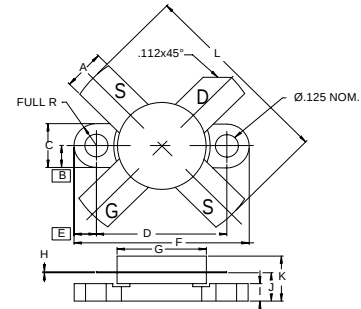
DESCRIPTION:

The **ASI BLF177** is a N-Channel Enhancement-Mode MOSFET RF Power Transistor Designed for industrial and military applications in the HF/ VHF frequency range.

MAXIMUM RATINGS

I_D	16 A
V_{DS}	110 V
V_{GS}	± 20 V
P_{DISS}	220 W @ $T_{mb} = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	0.8°C/W

PACKAGE STYLE .500 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.125 / 3.18	
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.730 / 18.54
E	.125 / 3.18	
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K		.280 / 7.11
L	.980 / 24.89	1.050 / 26.67

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	$I_D = 50$ mA	110			V
I_{DSS}	$V_{DS} = 50$ V $V_{GS} = 0$ V			2.5	mA
I_{GSS}	$V_{DS} = 0$ V $V_{GS} = \pm 20$ V			1.0	μA
$V_{GS(th)}$	$I_D = 50$ mA $V_{DS} = 10$ V	2.0		4.5	V
ΔV_{GS}	$I_D = 50$ mA $V_{DS} = 10$ V			100	mV
g_{fs}	$I_D = 5.0$ A $V_{DS} = 10$ V	4.5	6.2		S
$R_{DS(on)}$	$I_D = 5.0$ A $V_{DS} = 10$ V		0.2	0.3	Ω
I_{DSX}	$V_{GS} = 10$ V $V_{DS} = 10$ V		25		A
C_{is} C_{os} C_{rs}	$V_{DS} = 50$ V $V_{GS} = 0$ V $f = 1.0$ MHz		480 190 14		pF

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